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Zhang, Y., see Weber, W.J. ... 206 (2003) 1
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Zhu, S., X.T. Zu, X. Xiang, Z.G. Wang, L.M. Wang and R.C. Ewing, Electron microscopy and optical spectroscopy study of xenon-implanted yttria-stabilized zirconia ... 206 (2003) 1092
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